

Bias Resistor Transistor

PNP Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

LDTA113TKT1G

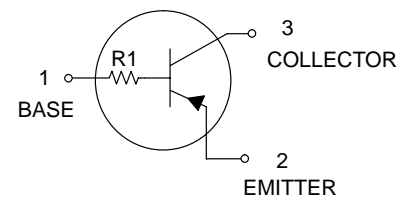
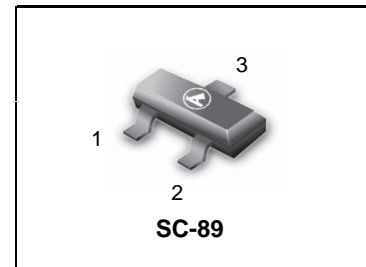
- **Applications**

Inverter, Interface, Driver

- **Features**

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on/off conditions need to be set for operation, making the device design easy.

- We declare that the material of product compliance with RoHS requirements.



- **Absolute maximum ratings** ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CB0}	-50	V
Collector-emitter voltage	V_{CE0}	-50	V
Emitter-base voltage	V_{EB0}	-5 to +10	V
Collector current	I_c	-100	mA
Collector Power dissipation	P_c	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

DEVICE MARKING AND RESISTOR VALUES

Device	Marking	R1 (K)	R2 (K)	Shipping
LDTA113TKT1G	O2	1	-	3000/Tape & Reel
LDTA113TKT3G	O2	1	-	10000/Tape & Reel

- **Electrical characteristics** ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CB0}	-50	-	-	V	$I_c = -50\mu\text{A}$
Collector-emitter breakdown voltage	BV_{CE0}	-50	-	-	V	$I_c = -1\text{mA}$
Emitter-base breakdown voltage	BV_{EB0}	-5	-	-	V	$I_E = -50\mu\text{A}$
Collector cutoff current	I_{cB0}	-	-	-0.5	μA	$V_{CB} = -50\text{V}$
Emitter cutoff current	I_{EB0}	-	-	-0.5	μA	$V_{EB} = -4\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-	-0.3	V	$I_c/I_E = -5\text{mA} / -0.25\text{mA}$
DC current transfer ratio	h_{FE}	100	250	600	-	$I_c = -1\text{mA}$, $V_{CE} = -5\text{V}$
Input resistance	R_1	0.7	1	1.3	$\text{k}\Omega$	-
Transition frequency	f_T *	-	250	-	MHz	$V_{CB} = -10\text{V}$, $I_E = 5\text{mA}$, $f = 100\text{MHz}$

* Characteristics of built-in transistor

LDTA113TKT1G

● **Electrical characteristic curves**

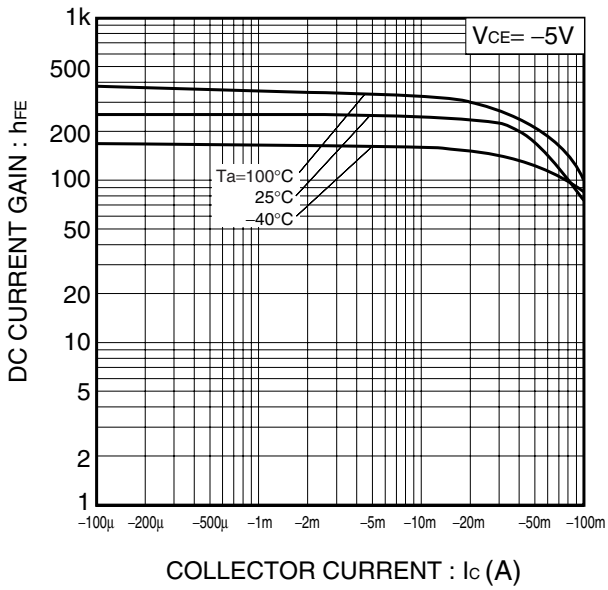


Fig.1 DC Current gain vs. Collector Current

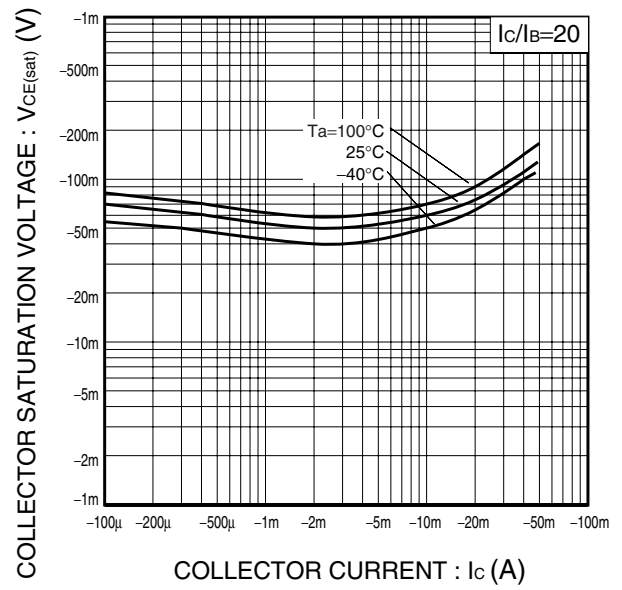
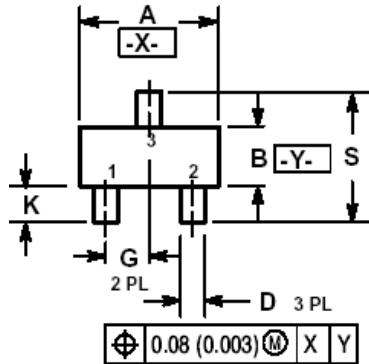
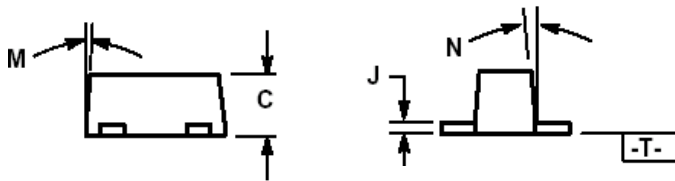


Fig.2 Collector-emitter saturation voltage vs. Collector Current

LDTA113TKT1G
SC-89

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 463C-01 OBSOLETE, NEW STANDARD 463C-02.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.60	1.70	0.059	0.063	0.067
B	0.75	0.85	0.95	0.030	0.034	0.040
C	0.60	0.70	0.80	0.024	0.028	0.031
D	0.23	0.28	0.33	0.009	0.011	0.013
G	0.50 BSC			0.020 BSC		
H	0.53 REF			0.021 REF		
J	0.10	0.15	0.20	0.004	0.006	0.008
K	0.30	0.40	0.50	0.012	0.016	0.020
L	1.10 REF			0.043 REF		
M	---	---	10 °	---	---	10 °
N	---	---	10 °	---	---	10 °
S	1.50	1.60	1.70	0.059	0.063	0.067

